

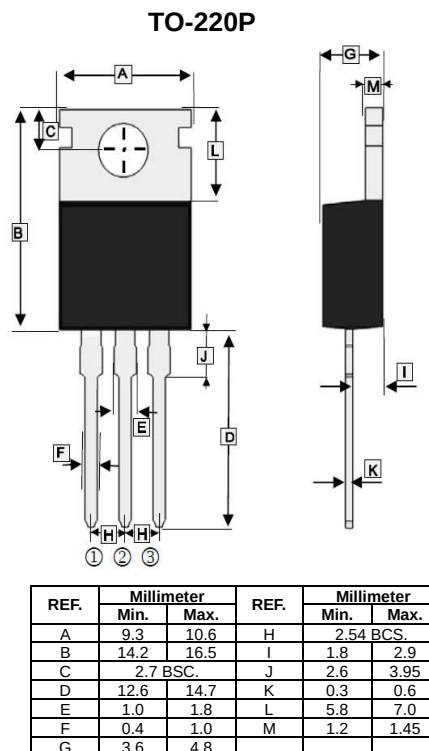
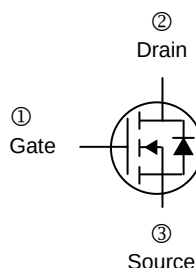
RoHS Compliant Product
A suffix of "-C" specifies halogen free

DESCRIPTION

The SSE04N60SL is the highest performance trench N-ch MOSFETs with extreme high cell density , which provide excellent $R_{DS(on)}$ and gate charge for most of the synchronous buck converter applications .

FEATURES

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	± 30	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	4	A
	$T_C=100^\circ\text{C}$		2.5	A
Pulsed Drain Current		I_{DM}	16	A
Total Power Dissipation	$T_C=25^\circ\text{C}$	P_D	100	W
	Derate above 25°C		0.8	
Single Pulse Avalanche Energy ¹		E_{AS}	217	mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$
Thermal Resistance Rating				
Maximum Thermal Resistance Junction-Ambient		$R_{\theta JA}$	62.5	$^\circ\text{C} / \text{W}$
Maximum Thermal Resistance Junction-Case		$R_{\theta JC}$	1.25	$^\circ\text{C} / \text{W}$

Notes:

1. $L=30\text{mH}$, $I_{AS}=3.45\text{A}$, $V_{DD}=155\text{V}$, $R_G=25\Omega$, Starting $T_J = 25^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	600	-	-	V	$V_{GS}=0$, $I_D=250\mu\text{A}$
Gate-Threshold Voltage	$V_{GS(th)}$	2	-	4	V	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$
Gate-Source Leakage Current	I_{GSS}	-	-	± 100	nA	$V_{GS}= \pm 30\text{V}$
Drain-Source Leakage Current	I_{DSS}	-	-	1	μA	$V_{DS}=600\text{V}$, $V_{GS}=0$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	2.0	2.4	Ω	$V_{GS}=10\text{V}$, $I_D=2\text{A}$
Total Gate Charge ^{1,2}	Q_g	-	8.16	-	nC	$I_D=4\text{A}$ $V_{DS}=480\text{V}$ $V_{GS}=10\text{V}$
Gate-Source Charge ^{1,2}	Q_{gs}	-	2.63	-		
Gate-Drain Change ^{1,2}	Q_{gd}	-	3.01	-		
Turn-on Delay Time ^{1,2}	$T_{d(on)}$	-	16.8	-	nS	$V_{DD}=300\text{V}$ $I_D=4\text{A}$ $R_G=25\Omega$
Rise Time ^{1,2}	T_r	-	26.2	-		
Turn-off Delay Time ^{1,2}	$T_{d(off)}$	-	37.4	-		
Fall Time ^{1,2}	T_f	-	20.2	-	pF	$V_{GS}=0$ $V_{DS}=25\text{V}$ $f=1.0\text{MHz}$
Input Capacitance	C_{iss}	-	449.7	-		
Output Capacitance	C_{oss}	-	57	-		
Reverse Transfer Capacitance	C_{rss}	-	2	-		
Source-Drain Diode						
Diode Forward Voltage	V_{SD}	-	-	1.4	V	$I_S=4\text{A}$, $V_{GS}=0$
Continuous Source Current	I_S	-	-	4	A	Integral Reverse P-N Junction Diode in the MOSFET
Pulsed Source Current	I_{SM}	-	-	16	A	
Reverse Recovery Time ¹	T_{rr}	-	441.53	-	ns	$I_S=4\text{A}$, $V_{GS}=0$, $di_f/dt=100\text{A}/\mu\text{S}$
Reverse Recovery Charge ¹	Q_{rr}	-	1.98	-	μC	

Notes:

1. Pulse Test: Pulse width $\leq 300\mu\text{S}$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature.

CHARACTERISTIC CURVES

Figure 1. On-Region Characteristics

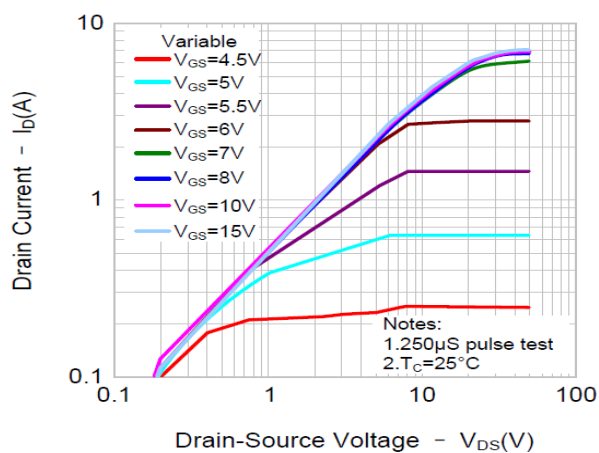


Figure 2. Transfer Characteristics

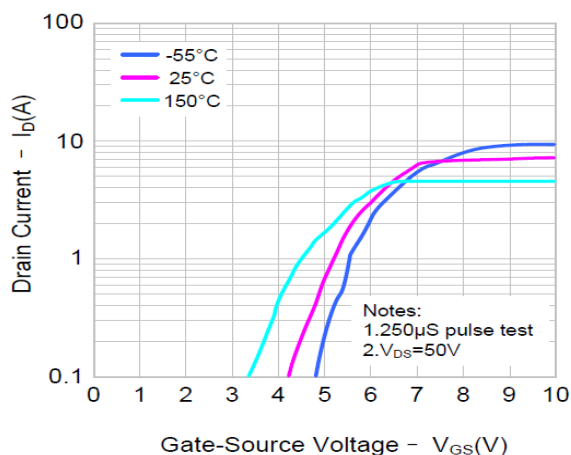


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

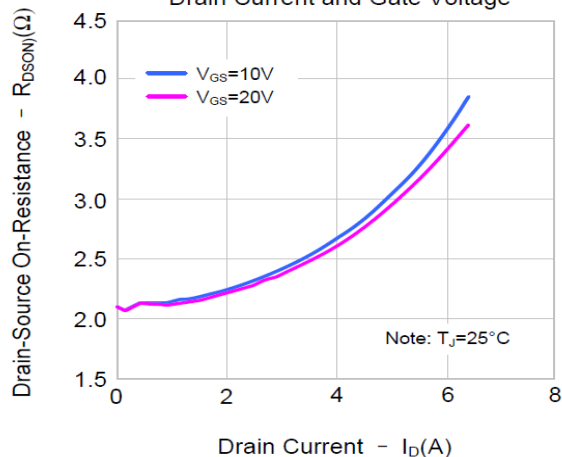


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

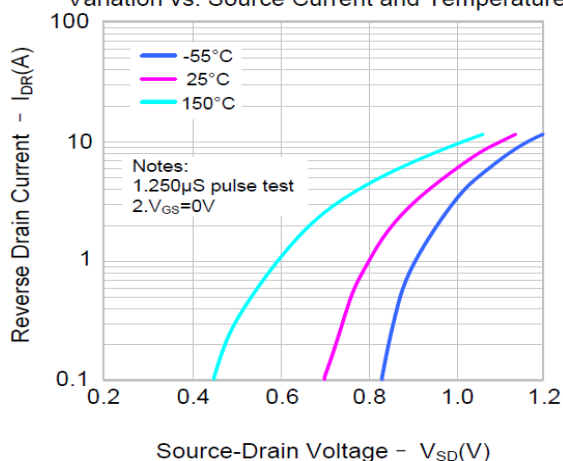


Figure 5. Capacitance Characteristics

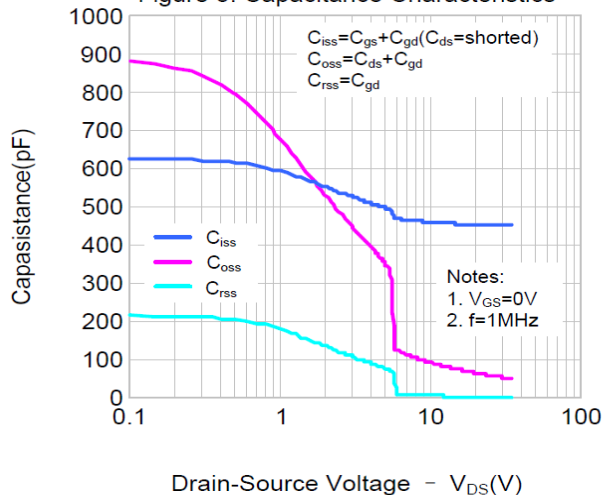
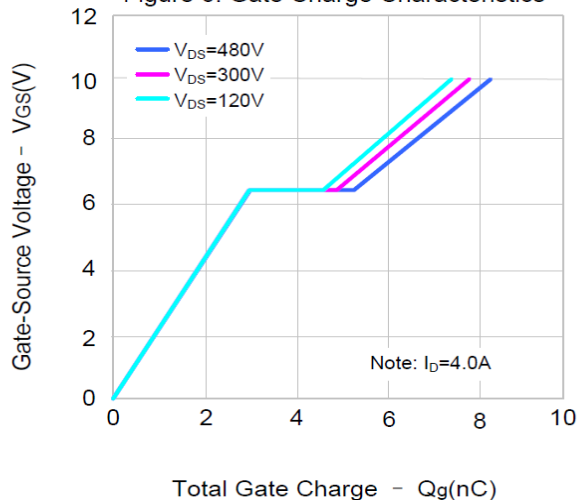


Figure 6. Gate Charge Characteristics



CHARACTERISTIC CURVES

Figure 7. Breakdown Voltage Variation vs. Temperature

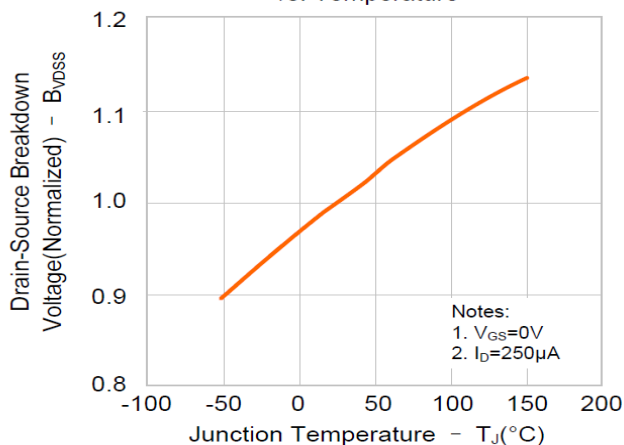


Figure 8. On-resistance Variation vs. Temperature

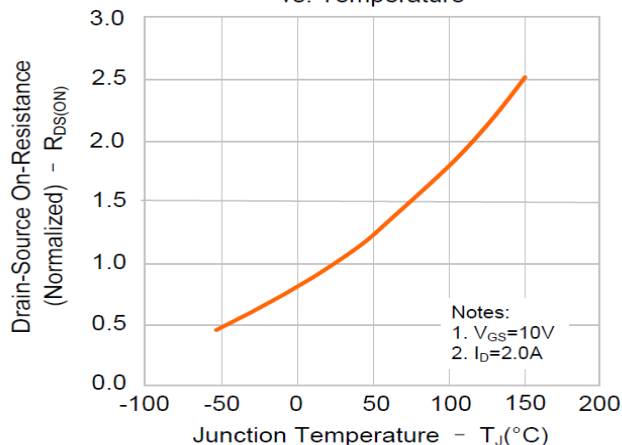


Figure 9 Max. Safe Operating Area

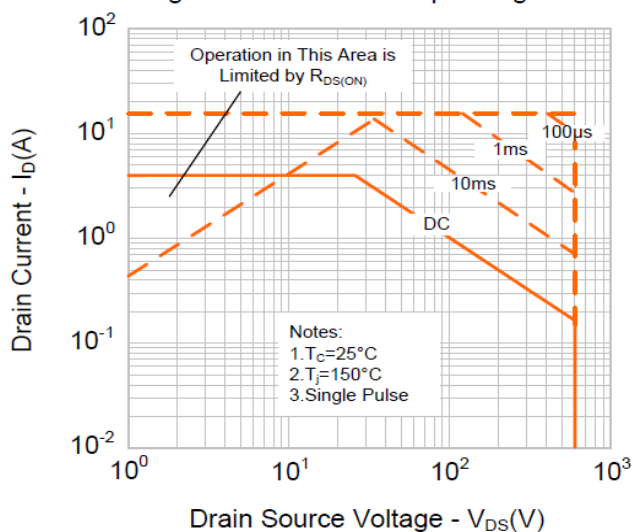
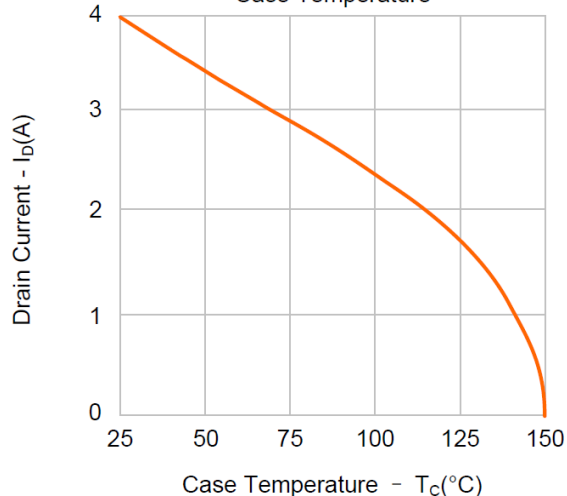
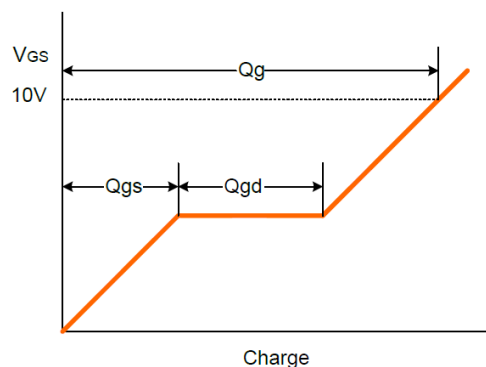
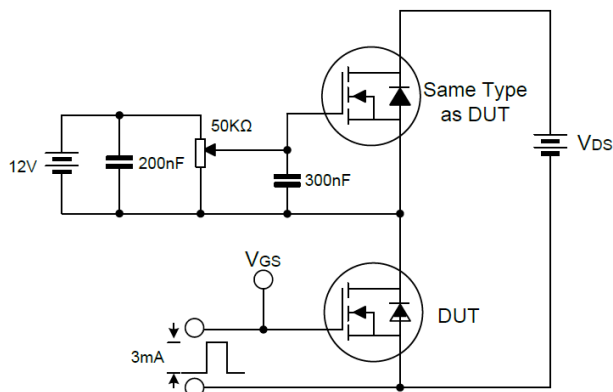


Figure 10. Maximum Drain Current vs. Case Temperature

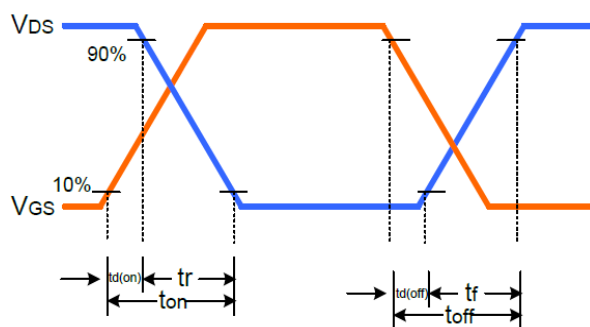
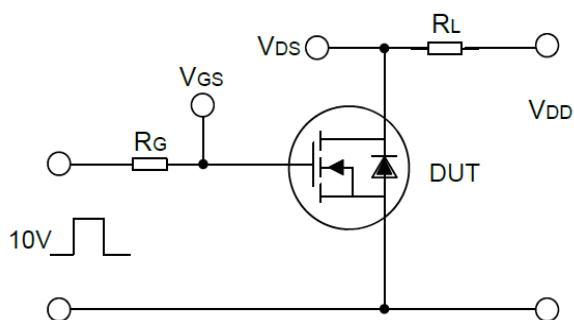


Gate Charge Test Circuit & Waveform



CHARACTERISTIC CURVES

Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform

